



PNP Silicon Planar High Voltage Transistor

SOT-23

Pin Definition:

- 1. Base
- 2. Emitter
- 3. Collector

PRODUCT SUMMARY

BV _{CBO}	-500V
BV _{CEO}	-500V
Ic	-150mA
V _{CE(SAT)}	$-0.5V @ I_C / I_B = -50mA / -10mA$

Ordering Information Features

 Low Saturation Voltages 			T	_
 Excellent gain characteristics specified up to -50mA 	Part No.	Package	Packing	
S4	TSA884CX RFG	SOT-23	3Kpcs / 7" Reel	

Note: "G" denotes for Halogen Free

Structure

- **Epitaxial Planar Type**
- PNP Silicon Transistor

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Collector-Base Voltage		V_{CBO}	-500	V	
Collector-Emitter Voltage		V_{CEO}	-500	V	
Emitter-Base Voltage		V_{EBO}	V _{EBO} -5		
Collector Current	DC		-150	A	
	Pulse	I _C	-500	- mA	
Total Power Dissipation		P _{TOT}	0.3	W	
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C	

Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$I_C = -100uA, I_E = 0$	BV_{CBO}	-500		1	V
Collector-Emitter Breakdown Voltage	$I_C = -10 \text{mA}, I_B = 0$	BV _{CEO}	-500		-	V
Emitter-Base Breakdown Voltage	$I_E = -100uA, I_C = 0$	BV_{EBO}	-5			V
Collector Cutoff Current	$V_{CB} = 120V, I_{E} = 0$	I _{CBO}	1		-100	nA
Emitter Cutoff Current	$V_{EB} = 6V, I_{C} = 0$	I _{EBO}	1		-100	nA
Collector-Emitter Saturation Voltage	$I_C = -20 \text{mA}, I_B = -2 \text{mA}$	V _{CE(SAT)} 1	ľ		-0.2	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
	$I_C = -50 \text{mA}, I_B = -10 \text{mA}$	V _{CE(SAT)} 2			-0.5	V
Base-Emitter Saturation Voltage	$I_C = -50 \text{mA}, I_B = -10 \text{mA}$	V _{BE(SAT)}	1		-0.9	V
Base-Emitter on Voltage	$V_{CE} = -10V, I_{C} = -50mA$	$V_{BE(ON)}$	-		-0.9	V
	$V_{CE} = -10V, I_{C} = -1mA$	h _{FE} 1	150		300	
DC Current Transfer Ratio	$V_{CE} = -10V, I_{C} = -50mA$	h _{FE} 2	80		300	
	$V_{CE} = -10V, I_{C} = -100mA$	h _{FE} 3	-	15		
Transition Frequency	$V_{CE} = 10V, I_{C} = -100mA$	f _T	-	50		MHz
Output Capacitance	$V_{CB} = 20V$, $f=1MHz$	Cob			8	pF
Turn On Time	$V_{CE} = -100V, I_{C} = -50mA$	Ton		110		nS
Turn Off Time	I _{B1} =-5mA, I _{B2} =-10mA	Toff		1500		nS







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Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

Figure 1. Static Characteristics

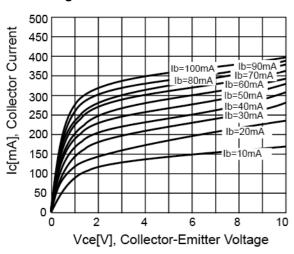


Figure 3. V_{CE(SAT)} v.s. V_{BE(SAT)}

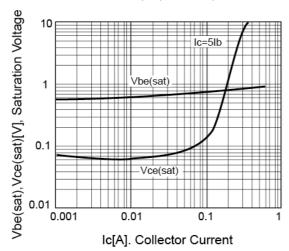


Figure 2. DC Current Gain

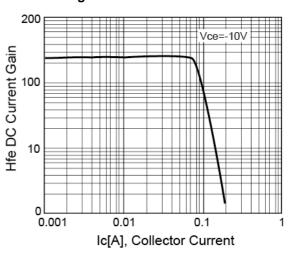
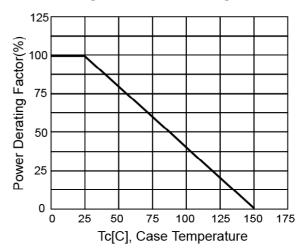


Figure 4. Power Derating

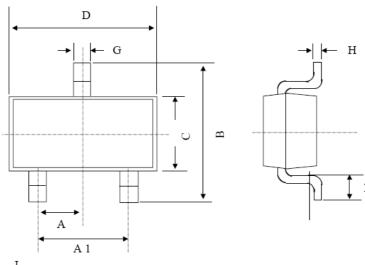




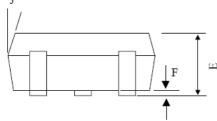


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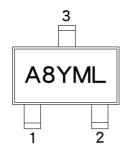
SOT-23 Mechanical Drawing



SOT-23 DIMENSION						
DIM	MILLIMETERS		INCHES			
DIIVI	MIN	MAX	MIN	MAX.		
Α	0.95 BSC		0.037 BSC			
A1	1.9	1.9 BSC		BSC		
В	2.60	3.00	0.102	0.118		
С	1.40	1.70	0.055	0.067		
D	2.80	3.10	0.110	0.122		
Е	1.00	1.30	0.039	0.051		
F	0.00	0.10	0.000	0.004		
G	0.35	0.50	0.014	0.020		
Н	0.10	0.20	0.004	0.008		
Ī	0.30	0.60	0.012	0.024		
J	5°	10°	5°	10°		



Marking Diagram



A8 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

3

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSA884

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